HALOGEN

FREE



2 Port, USB 2.0 High Speed (480 Mbps) Switch, DPDT Analog Switch

DESCRIPTION

The DG2730 is 2 port high speed analog switch optimized for USB 2.0 signal switching. The DG2730 switch is configured in DPDT. It handles bidirectional signal flow, achieving a 900 MHz -3 dB bandwidth, a port to port crosstalk at -36 dB and isolation at -29 dB, measured at 240 MHz.

Processed with high density sub micron CMOS, the DG2730 provide low parasitic capacitance. Signals are routed with minimized phase distortion and attain a bit to bit skew is as low as 40 ps.

The DG2730 is designed for a wide range of operating voltages, from 2.7 V to 5.5 V that can be driven directly from one cell Li-ion battery or 5 V power supply. On-chip circuitry protects against conditions when either the D+ / D-lines are shorted to the V_{BUS} at the USB port. Additionally, logic control pins (S and OE) can tolerate the presence of voltages that are above the supply power rail (V+). The control logic threshold is guaranteed to be (V_{IH} = 1.3 V/min up to V+ = 3.6 V). Latch up current is 500 mA, as per JESD78, and its ESD tolerance exceeds 5.5 kV.

Packaged in ultra small miniQFN-10 (1.4 mm \times 1.8 mm \times 0.55 mm), it is ideal for portable high speed mix signal switching application.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with lead (Pb)-free device termination. The miniQFN-10 package has a nickel-palladium-gold device termination and is represented by the lead (Pb)-free "-GE4" suffix to the ordering part number. The nickel-palladium-gold device terminations meet all JEDEC® standards for reflow and MSL rating.

As a further sign of Vishay Siliconix's commitment, the DG2730 is fully RoHS-complaint.

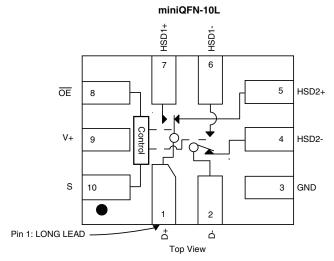
FEATURES

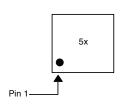
- Wide operation voltage range
- Low on-resistance, 5.5 Ω (typical at 3 V)
- Low capacitance, C_{ON} = 5.8 pF (typical)
- 3 dB high bandwidth: 900 MHz (typical)
- Low bit to bit skew: 40 ps (typical)
- Low power consumption
- Low logic threshold: V
- Power down protection: D+/D- pins can tolerate up to 5.5 V when V+ = 0 V
- 5.5 kV ESD protection (HBM)
- Latch-up current 500 mA per JESD78
- Lead (Pb)-free low profile miniQFN-10 (1.4 mm x 1.8 mm x 0.55 mm)
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- Cellular phones
- · Portable media players
- PDA
- Digital camera
- GPS
- Notebook computer
- TV, monitor, and set top box

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION





Device marking: 5x for DG2730 x = Date/Lot Traceability Code



www.vishay.com

Vishay Siliconix

ORDERING INFROMATION					
TEMP. RANGE	NGE PACKAGE PART NUMBER				
-40 °C to 85 °C	miniQFN-10	DG2730DN-T1-GE4			

TRUTH TABLE					
OE (PIN 8)	S (PIN 10)	FUNCTION			
0	1	D+ = HSD1+ and D- = HSD1-			
0	0	D+ = HSD2+ and D- = HSD2-			
1	Х	Disconnect			

PIN DESCRIPTIONS					
PIN NAME	DESCRIPTION				
ŌĒ	Bus switch enable				
S	Select input				
HSD1±, HSD2±, D±	Data port				

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)					
PARAMETER		LIMIT	UNIT		
Deference to CND	V+	-0.3 to 6	V		
Reference to GND	S, $\overline{\text{OE}}$, D±, HSD1±, HSD2± a	-0.3 to (V+ + 0.3)	7 '		
Current (Any Terminal Except S, OE, D±,	HSD1±, HSD2±)	30			
Continuous Current (S, OE, D±, HSD1±, HSD2±)		± 250	mA		
Peak Current (Pulsed at 1 ms, 10 % duty cycle)		± 500			
Storage Temperature (D suffix)		-65 to +150	°C		
Power Dissipation (Packages) b	miniQFN-10 °	208	mW		
ESD (Human body model)		5.5	kV		
Latch-Up (Current injection)		500	mA		

Notes

- a. Signals on S, $\overline{\text{OE}}$, D±, HSD1±, HSD2± exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC board.
- c. Derate 2.6 mW/°C above 70 °C.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Vishay Siliconix

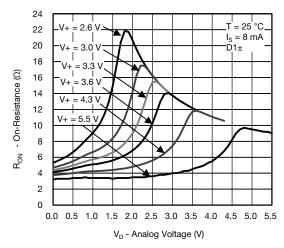
SPECIFICATIONS (V+ = 3 V)								
PARAMETER	SYMBOL	TEST CONDITIONS	TEMP. a	LIMITS -40 °C to +85 °C			UNIT	
		OTHERWISE UNLESS SPECIFIED		MIN. b	TYP.°	MAX. b		
Analog Switch								
Analog Signal Range d	V _{ANALOG}	R _{DS(on)}	Full	0	-	V+	٧	
On-Resistance	Book	$V+ = 3 \text{ V}, I_{D\pm} = 8 \text{ mA}, V_{HSD1/2\pm} = 0.4 \text{ V}$	Room	-	5.5	8		
On-nesistance	R _{DS(on)}	V+ - 0 V, ID± - 0 IIIA, VHSD1/2± - 0.4 V	Full	-	-	9	Ω	
On-Resistance Match d	ΔR_{ON}	V+ = 3 V, $I_{D\pm}$ = 8 mA, $V_{HSD1/2\pm}$ = 0.4 V	Room	-	0.8	-		
On-Resistance Flatness ^d	R _{ON} Flatness	V+ = 3 V, $I_{D\pm}$ = 8 mA, $V_{HSD1/2\pm}$ = 0 V, 1 V	Room	-	2	-		
Switch Off Leakage Current	l _{off}	$V+ = 4.3 \text{ V}, V_{HSD1/2\pm} = 0.3 \text{ V}, 3 \text{ V}, \\ V_{D\pm} = 3 \text{ V}, 0.3 \text{ V}$	Full	-100	ı	100	nΛ	
Channel On Leakage Current	I _{on}	$V+ = 4.3 \text{ V}, V_{HSD1/2\pm} = 0.3 \text{ V}, 4 \text{ V}, V_{D\pm} = 4 \text{ V}, 0.3 \text{ V}$	Full	-200	-	200	nA	
Digital Control								
Innut Valtage High	V	V+ = 3 V to 3.6 V	Full	1.3	-	-		
Input Voltage High	V_{INH}	V+ = 4.3 V	Full	1.5	-	-	٧	
Input Voltage Low	V _{INL}	V+ = 3 V to 4.3 V	Full	-	-	0.5		
Input Capacitance	C _{IN}		Full	-	6.5	-	pF	
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	-1	=.	1	μA	
Dynamic Characteristics								
Break-Before-Make Time d	t _{BBM}		Room	-	5	-	ns	
bleak-belole-iviake fillle			Full	-	5	-		
S OF Turn On Time d		V+ = 3 V, $V_{D1/2}$ $_{\pm}$ = 1.5 V, R_L = 50 Ω ,	Room	-	-	30		
S, OE Turn-On Time ^d		$C_L = 35 pF$	Full	-	-	30		
S, OE Turn-Off Time d	+		Room	-	-	25		
3, OE Turn-On Time	t _{OFF}		Full	-	-	25		
Charge Injection ^d	Q_{INJ}	C_L = 1 nF, R_{GEN} = 0 Ω , V_{GEN} = 0 V		-	3	-	рС	
Off-Isolation d	OIRR	V+ = 3 V to 3.6 V, R_L = 50 Ω , C_L = 5 pF,		-	-29	-	- dB	
Crosstalk d, e	X _{TALK}	f = 240 MHz		-	-36	-		
Bandwidth ^d	BW	V+ = 3 V to 3.6 V, R_L = 50 $\Omega,$ - 3 dB		-	900	-	MHz	
D+/D- On Capacitance	C _{ON}	$V+ = 3.3 V$, $\overline{OE} = 0 V$, $f = 240 MHz$	Room	-	5.8	-	pF	
D1n, D2n Off Capacitance	C _{OFF}	$V + = \overline{OE} = 3.3 \text{ V, f} = 240 \text{ MHz}$		-	2.2	-		
Channel-to-Channel Skew d	t _{SK(O)}			-	50	-		
Skew Off Opposite Transitions of the Same Output ^d	t _{SK(p)}	V+ = 3 V to 3.6 V, R_L = 50 Ω , C_L = 5 pF		-	20	-	ps	
Total Jitter d	tJ			-	200	-		
Power Supply								
Power Supply Range	V+		-	2.6	-	5.5	V	
Power Supply Current	l+	V _{IN} = 0 V, or V+	Full	-	-	2	μΑ	

Notes

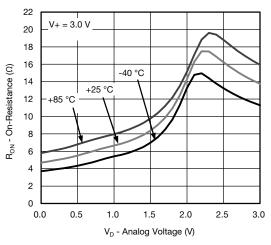
- a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- c. Typical values are for design aid only, not guaranteed nor subject to production testing.
- d. Guaranteed by design, not subjected to production test.
- e. Crosstalk measured between channels.



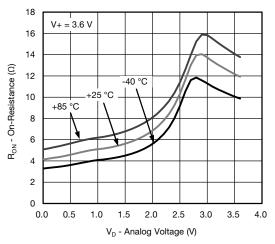
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



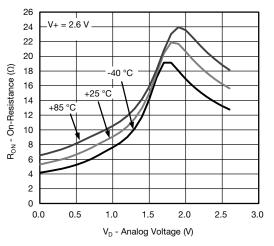
R_{ON} vs. V_D and Single Supply Voltage



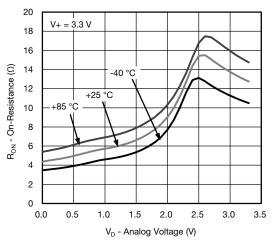
R_{ON} vs. Analog Voltage and Temperature



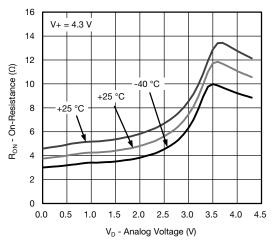
R_{ON} vs. Analog Voltage and Temperature



R_{ON} vs. Analog Voltage and Temperature



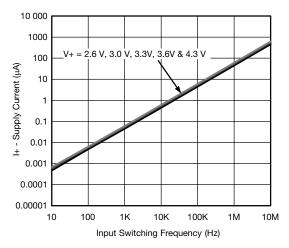
R_{ON} vs. Analog Voltage and Temperature



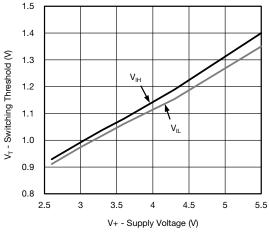
R_{ON} vs. Analog Voltage and Temperature



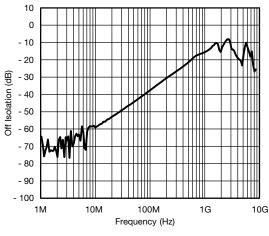
TYPICAL CHARACTERISTICS(T_A = 25 °C, unless otherwise noted)



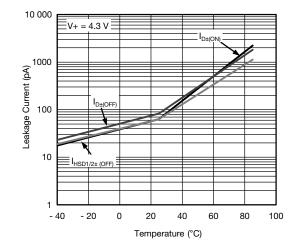
Supply Current vs. Input Switching Frequency



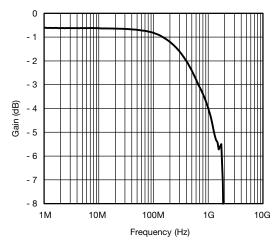
Switching Threshold vs. Supply Voltage



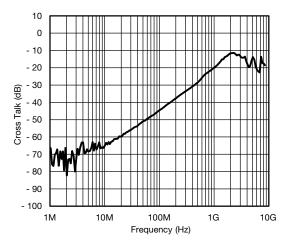
Off-Isolation, V+ = 3.3 V



Leakage Current vs. Temperature



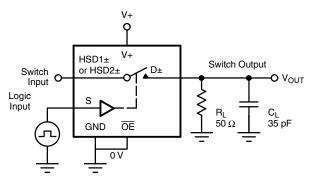
Gain vs. Frequency, V+ = 3.3 V



Crosstalk, V+ = 3.3 V

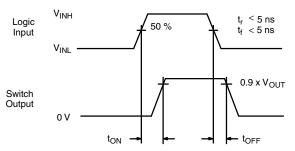


TEST CIRCUITS



C_L (includes fixture and stray capacitance)

$$V_{OUT} = \ D \pm \ \left(\frac{R_L}{R_L + R_{ON}} \right)$$



Logic "1" = Switch on Logic input waveforms inverted for switches that have the opposite logic sense.

Fig. 1 - Switching Time

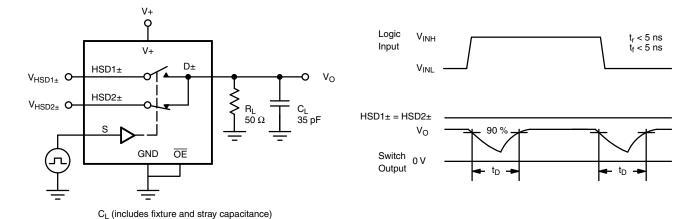


Fig. 2 - Break-Before-Make Interval

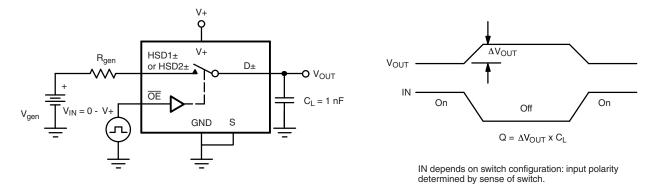


Fig. 3 - Charge Injection



TEST CIRCUITS

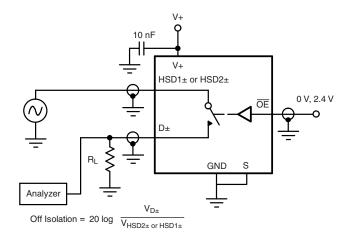


Fig. 4 - Off-Isolation

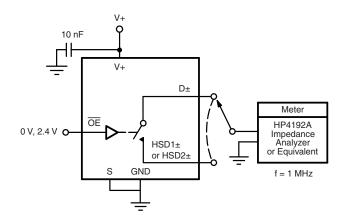
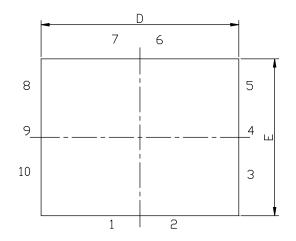


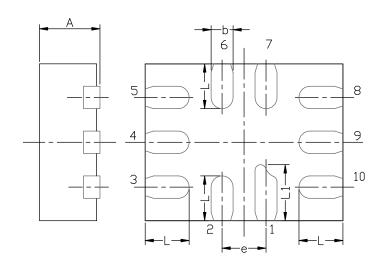
Fig. 5 - Channel Off/On Capacitance

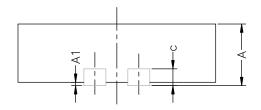
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67786

Vishay Siliconix

MINI QFN-10L CASE OUTLINE







DIM	MILLIMETERS			INCHES		
	MIN.	NAM.	MAX.	MIN.	NAM.	MAX.
A	0.45	0.55	0.60	0.0177	0.0217	0.0236
A1	0.00	-	0.05	0.000	-	0.002
b	0.15	0.20	0.25	0.006	0.008	0.010
С		0.150 or 0.127 REF ⁽	1)	0.006 or 0.005 REF ⁽¹⁾		
D	1.70	1.80	1.90	0.067	0.071	0.075
E	1.30	1.40	1.50	0.051	0.055	0.059
е		0.40 BSC			0.016 BSC	
L	0.35	0.40	0.45	0.014	0.016	0.018
L1	0.45	0.50	0.55	0.0177	0.0197	0.0217

Note

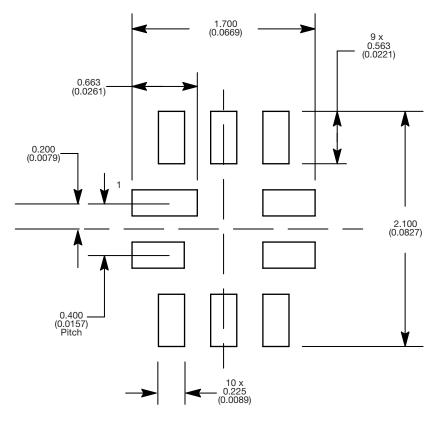
ECN T16-0163-Rev. B, 16-May-16 DWG: 5957

⁽¹⁾ The dimension depends on the leadframe that assembly house used.



Vishay Siliconix

RECOMMENDED MINIMUM PADS FOR MINI QFN 10L



Mounting Footprint Dimensions in mm (inch)



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

单击下面可查看定价,库存,交付和生命周期等信息

>>Vishay(威世)